

IN THE CLAIMS

Please amend the claims as follows:

1. (Currently Amended) A semiconductor device comprising:
  - a semiconductor substrate;
  - a conductive plug electrically connected to the semiconductor substrate and including Si;
  - a flat electrically conductive silicon carbide film provided on the conductive plug;
  - a capacitor comprising a lower flat electrode, a dielectric film on the lower flat electrode, and an upper electrode on the dielectric film, the lower flat electrode comprising a noble metal provided above the silicon carbide film; and
  - an adhesive layer provided between the silicon carbide film and the lower flat electrode and the adhesive layer comprising a flat metal carbide film configured to adhere the silicon carbide film [[to]] and the lower flat electrode.
2. (Withdrawn) A semiconductor device comprising:
  - a semiconductor substrate;
  - a conductive plug electrically connected to the semiconductor substrate;
  - a silicon carbide film provided on the conductive plug;
  - a metal compound film provided on the silicon carbide film and containing a metal carbide;
  - a capacitor lower electrode provided on the metal compound film;
  - a capacitor upper electrode provided above the capacitor lower electrode; and
  - a capacitor dielectric film provided between the capacitor lower electrode and the capacitor upper electrode and containing a ferroelectric material or a highly dielectric material as a major component.

3. (Original) The semiconductor device according to claim 1, wherein the conductive plug is electrically connected to an active region of a transistor provided on the surface of the semiconductor substrate.

4. (Withdrawn) The semiconductor device according to claim 2, wherein the conductive plug is electrically connected to an active region of a transistor provided on the surface of the semiconductor substrate.

5. (Original) The semiconductor device according to claim 1, wherein the metal carbide contains a carbide of titanium, zirconium, hafnium, vanadium, niobium, or tantalum.

6. (Withdrawn) The semiconductor device according to claim 2, wherein the metal carbide contains a carbide of titanium, zirconium, hafnium, vanadium, niobium, or tantalum.

7. (Original) The semiconductor device according to claim 3, wherein the metal carbide contains a carbide of titanium, zirconium, hafnium, vanadium, niobium, or tantalum.

8. (Withdrawn) The semiconductor device according to claim 4, wherein the metal carbide contains a carbide of titanium, zirconium, hafnium, vanadium, niobium, or tantalum.

9. (Currently Amended) The semiconductor device according to claim 1, wherein the ~~flat metal compound film~~ adhesive layer film further contains a compound of a metal contained in the metal carbide and silicon.

10. (Withdrawn) The semiconductor device according to claim 2, wherein the metal compound film further contains a compound of a metal contained in the metal carbide and silicon.

11. (Currently Amended) The semiconductor device according to claim 3, wherein the ~~flat metal compound film~~ adhesive layer further contains a compound of a metal contained in the metal carbide and silicon.

12. (Withdrawn) The semiconductor device according to claim 4, wherein the metal compound film further contains a compound of a metal contained in the metal carbide and silicon.

13. (Currently Amended) The semiconductor device according to claim 5, wherein the ~~flat metal compound film~~ adhesive layer further contains a compound of a metal contained in the metal carbide and silicon.

14. (Withdrawn) The semiconductor device according to claim 6, wherein the metal compound film further contains a compound of a metal contained in the metal carbide and silicon.

15. (Currently Amended) The semiconductor device according to claim 7, wherein the ~~flat metal compound film~~ adhesive layer further contains a compound of a metal contained in the metal carbide and silicon.

16. (Withdrawn) The semiconductor device according to claim 8, wherein the metal compound film further contains a compound of a metal contained in the metal carbide and silicon.

17. (Withdrawn) A method of manufacturing a semiconductor device comprising:  
preparing a semiconductor substrate;  
forming a conductive plug electrically connected to the semiconductor substrate;  
forming a silicon carbide film covering an upper surface of the conductive plug;  
forming a first metal film on the silicon carbide film;  
forming a second metal film on the first metal film;  
forming a dielectric film containing a ferroelectric material or a highly dielectric material which is a major component on the second metal film; and  
forming a metal compound film on the silicon carbide film by heat treatment in an oxidizing atmosphere, the metal compound film comprising a metal carbide of a metal contained in the first metal film and carbon.

18. (Withdrawn) The method according to claim 17, wherein the first metal film is a titanium film, zirconium film, hafnium film, vanadium film, niobium film, or tantalum film.

19. (Withdrawn) The method according to claim 17, further comprising: forming a third metal film on the metal compound film; processing the third metal film, the metal compound film, the dielectric film, the second metal film, and the silicon carbide film by etching; and carrying out a heat treatment in an oxidizing atmosphere.

20. (Withdrawn) The method according to claim 18, further comprising: forming a third metal film on the metal compound film; processing the third metal film, the metal compound film, the dielectric film, the second metal film, and the silicon carbide film by etching; and carrying out a heat treatment in an oxidizing atmosphere.

21. (Withdrawn) The method according to claim 17, wherein the dielectric film is a capacitor dielectric film, and the second and third metal films are capacitor lower and upper electrodes.

22. (Withdrawn) The method according to claim 18, wherein the dielectric film is a capacitor dielectric film, and the second and third metal films are capacitor lower and upper electrodes.

23. (Withdrawn) The method according to claim 19, wherein the dielectric film is a capacitor dielectric film, and the second and third metal films are capacitor lower and upper electrodes.

24. (Withdrawn) The method according to claim 20, wherein the dielectric film is a capacitor dielectric film, and the second and third metal films are capacitor lower and upper electrodes.